



General Description

- Trench Power MOSFET - AlphaSGT™ technology
- Low R_{DS(ON)}
- Excellent Gate Charge x R_{DS(ON)} Product (FOM)
- RoHS and Halogen-Free Compliant

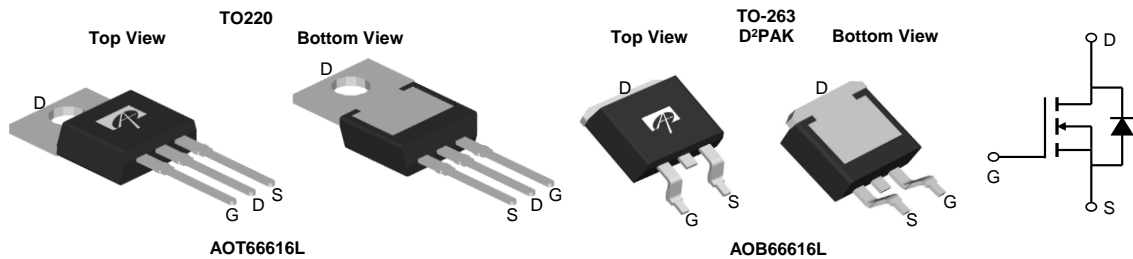
Applications

- Synchronous Rectification in DC/DC and AC/DC Converters
- Industrial and Motor Drive applications

Product Summary

V _{DS}	60V
I _D (at V _{GS} =10V)	140A
R _{DS(ON)} (at V _{GS} =10V)	< 3.2mΩ
R _{DS(ON)} (at V _{GS} =6V)	< 4.6mΩ

100% UIS Tested
100% R_g Tested



Orderable Part Number	Package Type	Form	Minimum Order Quantity
AOT66616L	TO-220	Tube	1000
AOB66616L	TO-263	Tape & Reel	800

Absolute Maximum Ratings T_A=25°C unless otherwise noted

Parameter	Symbol	Maximum	Units
Drain-Source Voltage	V _{DS}	60	V
Gate-Source Voltage	V _{GS}	±20	V
Continuous Drain Current ^G	I _D	T _C =25°C	140
		T _C =100°C	95
Pulsed Drain Current ^C	I _{DM}	330	A
Continuous Drain Current	I _{DSM}	T _A =25°C	38.5
		T _A =70°C	30.5
Avalanche Current ^C	I _{AS}	35	A
Avalanche energy L=0.3mH ^C	E _{AS}	184	mJ
Power Dissipation ^B	P _D	T _C =25°C	125
		T _C =100°C	50
Power Dissipation ^A	P _{DSM}	T _A =25°C	8.3
		T _A =70°C	5.3
Junction and Storage Temperature Range	T _J , T _{STG}	-55 to 150	°C

Thermal Characteristics

Parameter	Symbol	Typ	Max	Units
Maximum Junction-to-Ambient ^A t ≤ 10s	R _{θJA}	12	15	°C/W
Maximum Junction-to-Ambient ^{A,D} Steady-State		50	60	°C/W
Maximum Junction-to-Case Steady-State	R _{θJC}	0.8	1.0	°C/W

Electrical Characteristics (T_J=25°C unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
STATIC PARAMETERS						
BV _{DSS}	Drain-Source Breakdown Voltage	I _D =250μA, V _{GS} =0V	60			V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =60V, V _{GS} =0V T _J =55°C			1 5	μA
I _{GSS}	Gate-Body leakage current	V _{DS} =0V, V _{GS} =±20V			±100	nA
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D =250μA	2.4	2.9	3.4	V
R _{DS(on)}	Static Drain-Source On-Resistance	V _{GS} =10V, I _D =20A T _J =125°C		2.5 4.0	3.2 5.1	mΩ
		V _{GS} =6V, I _D =20A		3.4	4.6	mΩ
g _{FS}	Forward Transconductance	V _{DS} =5V, I _D =20A		100		S
V _{SD}	Diode Forward Voltage	I _S =1A, V _{GS} =0V		0.7	1	V
I _S	Maximum Body-Diode Continuous Current				135	A
DYNAMIC PARAMETERS						
C _{iss}	Input Capacitance	V _{GS} =0V, V _{DS} =30V, f=1MHz		2870		pF
C _{oss}	Output Capacitance			940		pF
C _{rss}	Reverse Transfer Capacitance			38		pF
R _g	Gate resistance	f=1MHz	0.6	1.25	1.9	Ω
SWITCHING PARAMETERS						
Q _{g(10V)}	Total Gate Charge	V _{GS} =10V, V _{DS} =30V, I _D =20A		42.5	60	nC
Q _{gs}	Gate Source Charge			12		nC
Q _{gd}	Gate Drain Charge			10		nC
Q _{oss}	Output Charge	V _{GS} =0V, V _{DS} =30V		54		nC
t _{D(on)}	Turn-On DelayTime	V _{GS} =10V, V _{DS} =30V, R _L =1.5Ω, R _{GEN} =3Ω		14.5		ns
t _r	Turn-On Rise Time			15.5		ns
t _{D(off)}	Turn-Off DelayTime			33		ns
t _f	Turn-Off Fall Time			12.5		ns
t _{rr}	Body Diode Reverse Recovery Time	I _F =20A, di/dt=500A/μs		26		ns
Q _{rr}	Body Diode Reverse Recovery Charge	I _F =20A, di/dt=500A/μs		87		nC

A. The value of R_{θJA} is measured with the device mounted on 1in² FR-4 board with 2oz. Copper, in a still air environment with T_A=25° C. The Power dissipation P_{DSM} is based on R_{θJA} ≤ 10s and the maximum allowed junction temperature of 150° C. The value in any given application depends on the user's specific board design.

B. The power dissipation P_D is based on T_{J(MAX)}=150° C, using junction-to-case thermal resistance, and is more useful in setting the upper dissipation limit for cases where additional heatsinking is used.

C. Single pulse width limited by junction temperature T_{J(MAX)}=150° C.

D. The R_{θJA} is the sum of the thermal impedance from junction to case R_{θJC} and case to ambient.

E. The static characteristics in Figures 1 to 6 are obtained using <300μs pulses, duty cycle 0.5% max.

F. These curves are based on the junction-to-case thermal impedance which is measured with the device mounted to a large heatsink, assuming a maximum junction temperature of T_{J(MAX)}=150° C. The SOA curve provides a single pulse rating.

G. The maximum current rating is package limited.

H. These tests are performed with the device mounted on 1 in² FR-4 board with 2oz. Copper, in a still air environment with T_A=25° C.

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TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

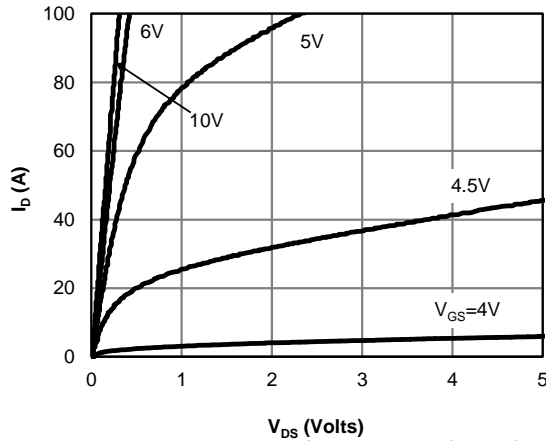


Figure 1: On-Region Characteristics (Note E)

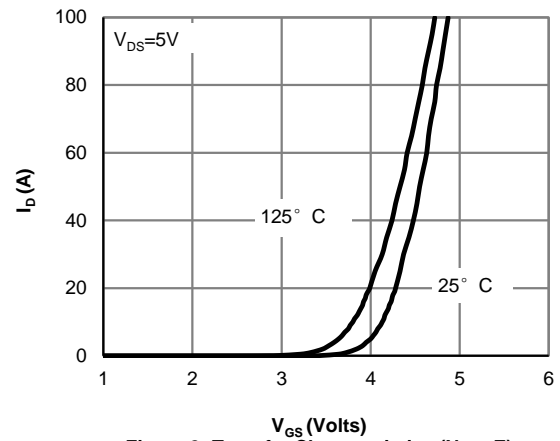


Figure 2: Transfer Characteristics (Note E)

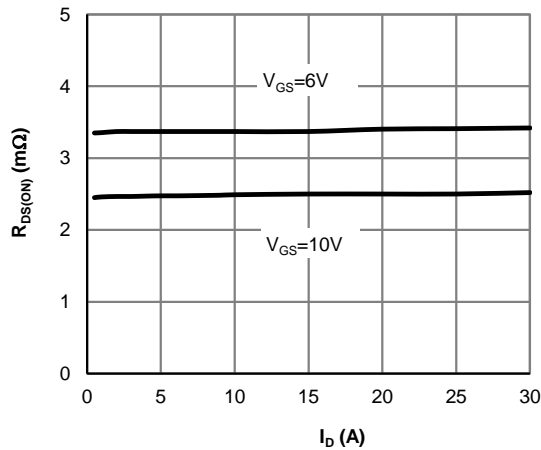


Figure 3: On-Resistance vs. Drain Current and Gate Voltage (Note E)

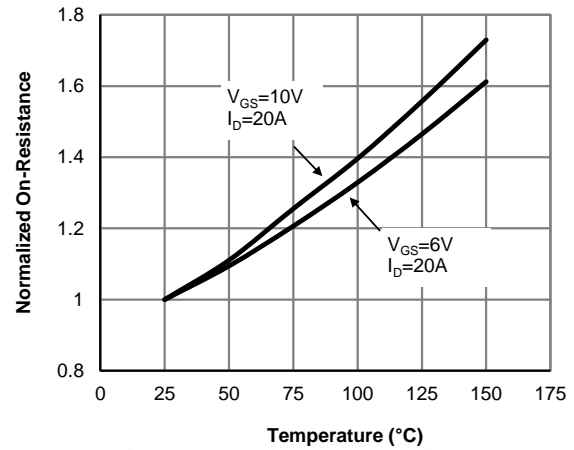


Figure 4: On-Resistance vs. Junction Temperature (Note E)

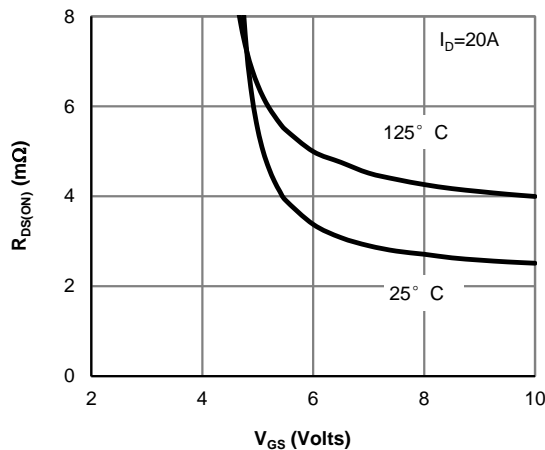


Figure 5: On-Resistance vs. Gate-Source Voltage (Note E)

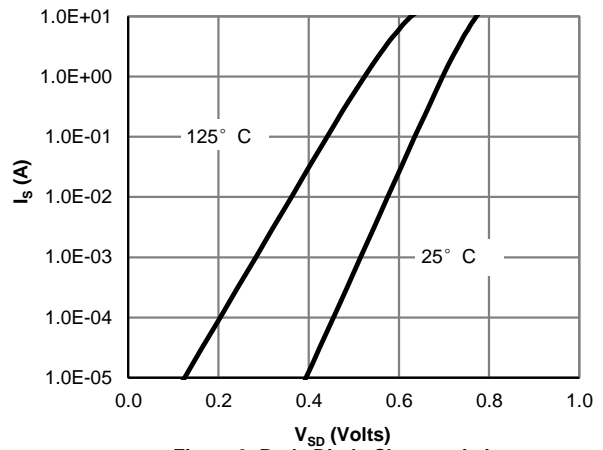


Figure 6: Body-Diode Characteristics (Note E)

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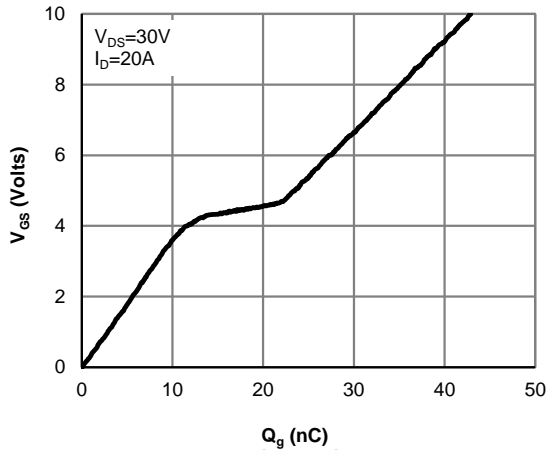


Figure 7: Gate-Charge Characteristics

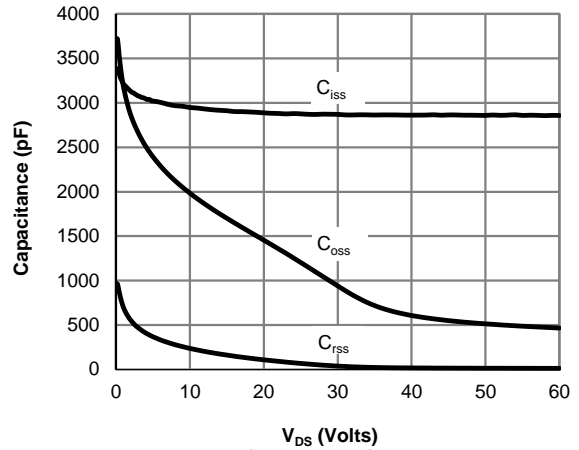


Figure 8: Capacitance Characteristics

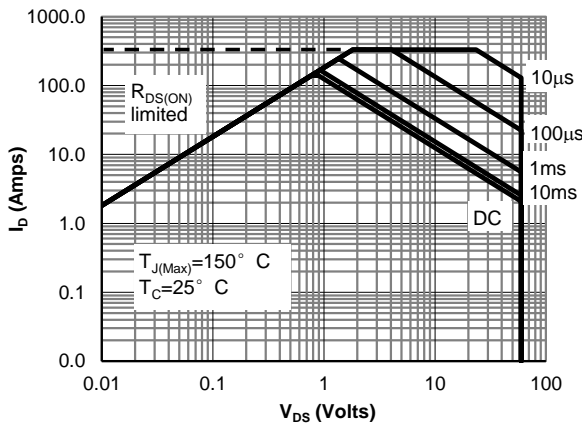


Figure 9: Maximum Forward Biased Safe Operating Area (Note F)

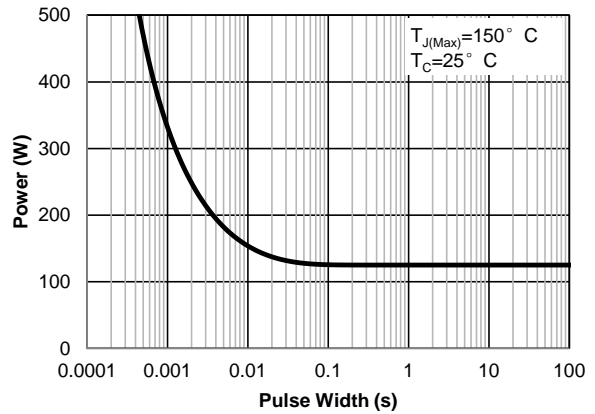


Figure 10: Single Pulse Power Rating Junction-to-Case (Note F)

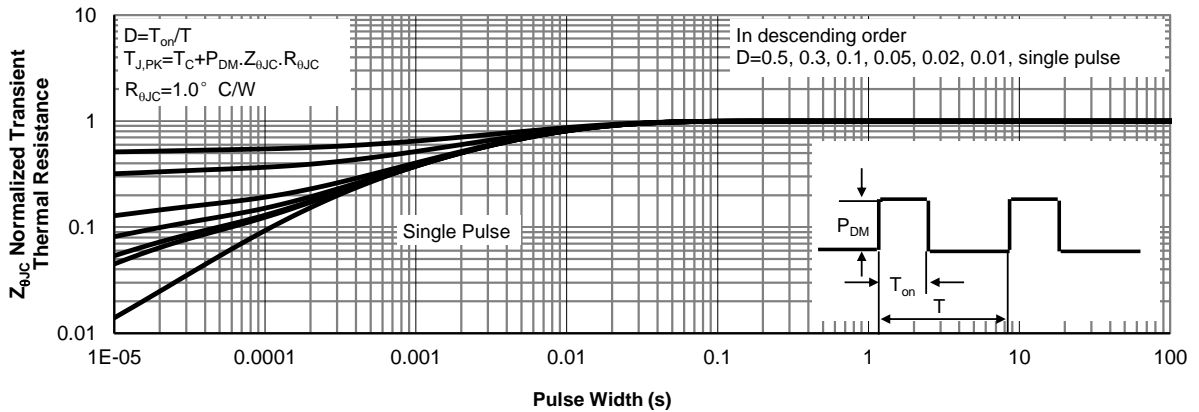


Figure 11: Normalized Maximum Transient Thermal Impedance (Note F)

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

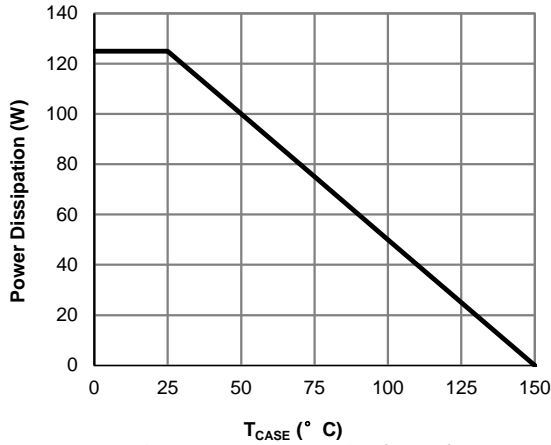


Figure 12: Power De-rating (Note F)

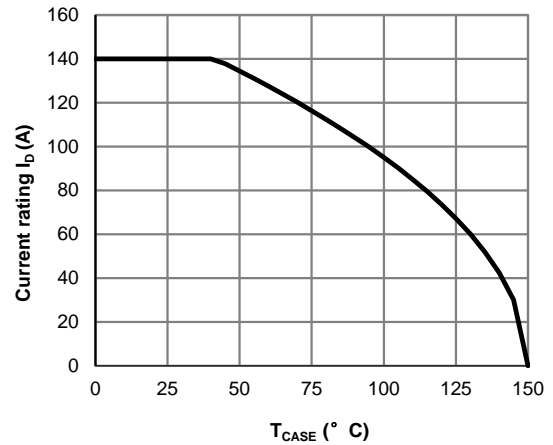


Figure 13: Current De-rating (Note F)

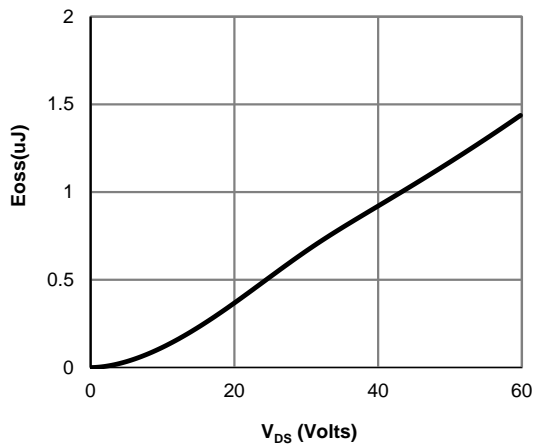


Figure 14: Coss stored Energy

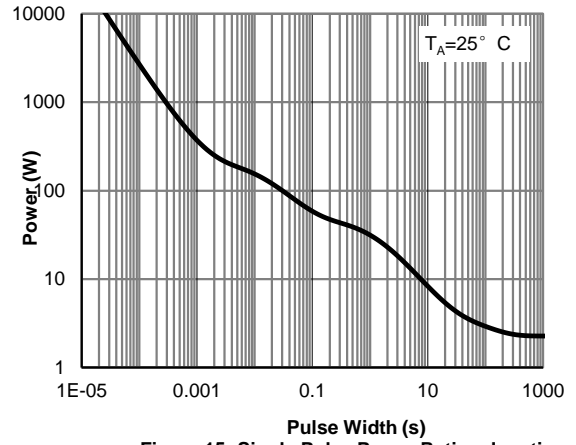


Figure 15: Single Pulse Power Rating Junction-to-Ambient (Note H)

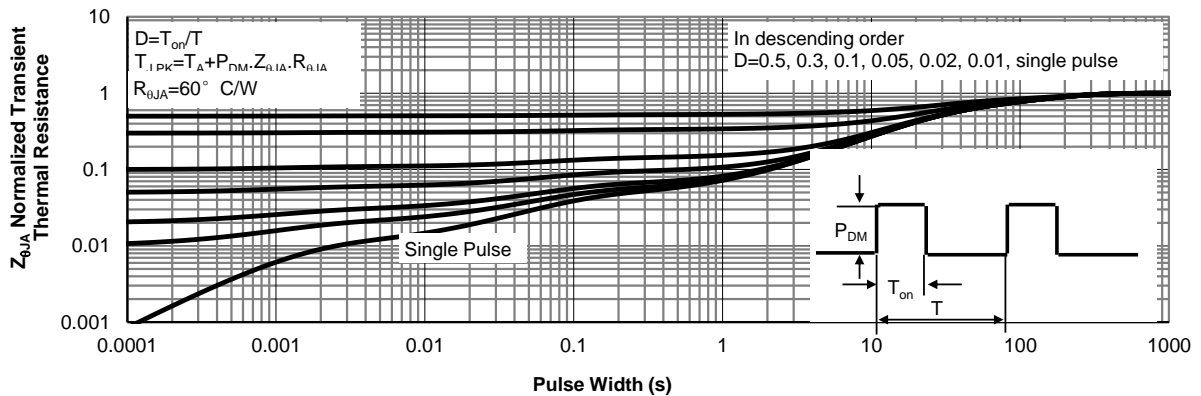


Figure 16: Normalized Maximum Transient Thermal Impedance (Note H)

Figure A: Gate Charge Test Circuit & Waveforms

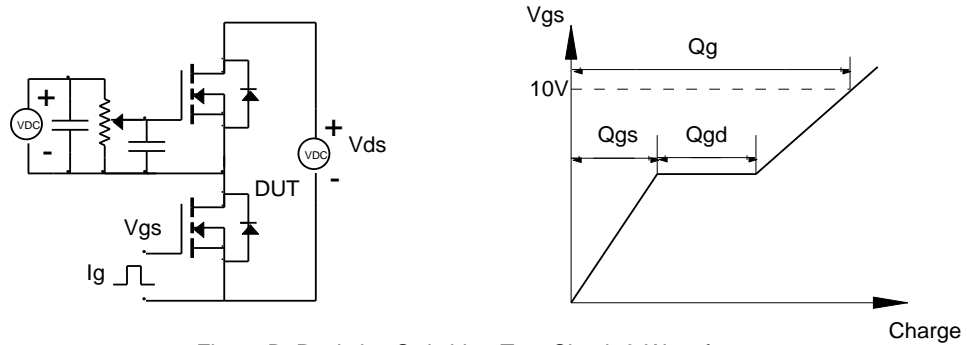


Figure B: Resistive Switching Test Circuit & Waveforms

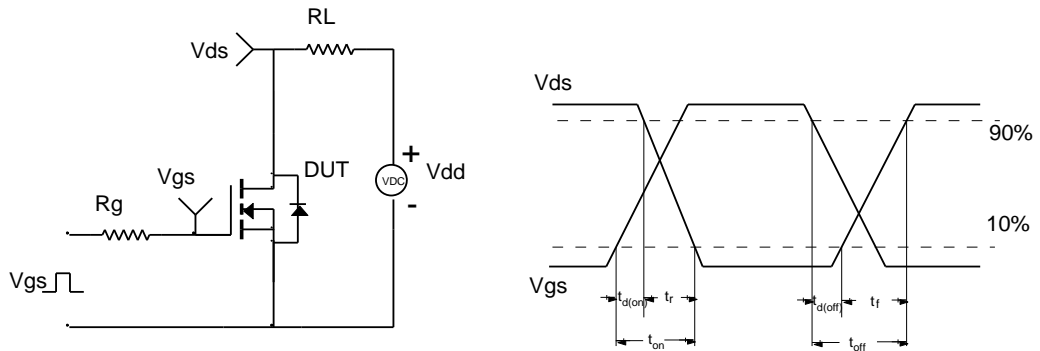


Figure C: Unclamped Inductive Switching (UIS) Test Circuit & Waveforms

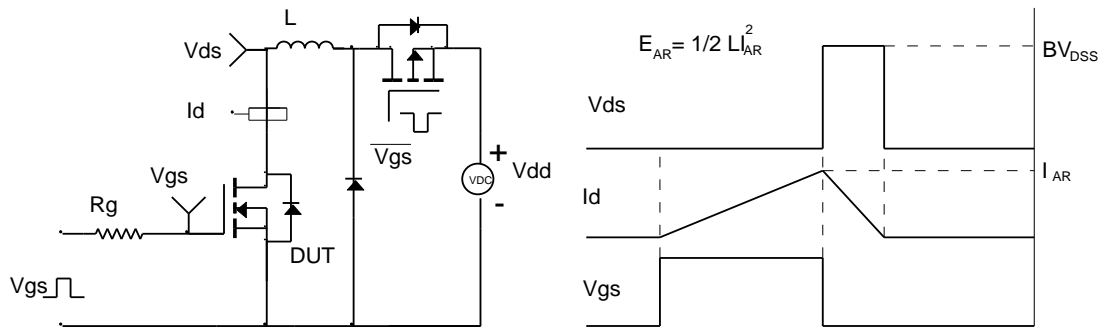


Figure D: Diode Recovery Test Circuit & Waveforms

